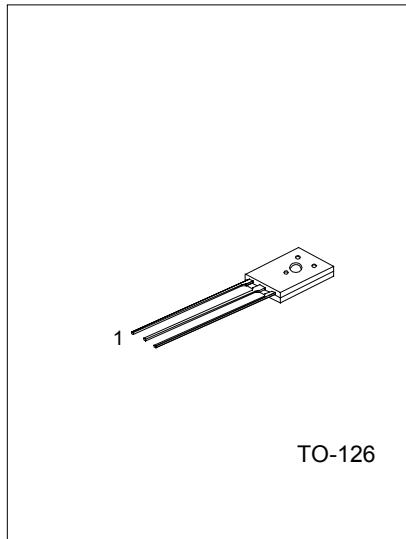
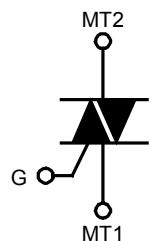


## TRIACS

## DESCRIPTION

Glass passivated triacs in a plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

## SYMBOL



1:MT1    2:MT2    3:GATE

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Repetitive peak off-state voltages UT134F/G-5 UT134F/G-6 UT134F/G-8	$V_{DRM}$	500 600* 800	V
RMS on-state current full sine wave; $T_{mb} \leq 107^\circ C$	$I_T(RMS)$	4	A
Non-repetitive peak on-state current (Full sine wave; $T_j = 25^\circ C$ prior to surge) $t = 20ms$ $t = 16.7 ms$	$I_{TSM}$	25 27	A
$I^2t$ for fusing $t = 10 ms$	$I^2t$	3.1	$A^2s$
Repetitive rate of rise of on-state current after triggering $I_{TM} = 6 A$ ; $I_G = 0.2A$ ; $dI_G/dt = 0.2A/\mu s$	$dI_T/dt$	50 50 50 10	$A/\mu s$
Peak gate voltage	$V_{GM}$	5	V
Peak gate current	$I_{GM}$	2	A
Peak gate power	$P_{GM}$	5	W
Average gate power (over any 20 ms period)	$P_{G(AV)}$	0.5	W
Storage temperature	$T_{stg}$	-40 ~ 150	°C
Operating junction temperature	$T_j$	125	°C

## UTC UT134F/G

## TRIAC

\*Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 3A/ $\mu$ s.

### THERMAL RESISTANCES

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Thermal resistance Junction to mounting base Full cycle	$R_{th\ j\-\text{mb}}$			3.0	K/W
Half cycle				3.7	K/W
Thermal resistance Junction to ambient (In free air)	$R_{th\ j\-\text{a}}$	100			K/W

### STATIC CHARACTERISTICS ( $T_j=25^\circ\text{C}$ , unless otherwise stated)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX		UNIT
					UT134F	UT134G	
Gate trigger current	$I_{GT}$	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$ T2+ G+ T2+ G- T2- G- T2- G+		5 8 11 30	25 25 25 70	50 50 50 100	mA
Latching current	$I_L$	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$ T2+ G+ T2+ G- T2- G- T2- G+		7 16 5 7	20 30 20 30	30 45 30 45	mA
Holding current	$I_H$	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$		5	15	30	mA
On-state voltage	$V_T$	$I_T = 5 \text{ A}$		1.4	1.7		V
Gate trigger voltage	$V_{GT}$	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$ $V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125^\circ\text{C}$	0.25	0.4			V
Off-state leakage current	$I_D$	$V_D = V_{DRM(\text{max})}; T_j = 125^\circ\text{C}$		0.1	0.5		mA

### DYNAMIC CHARACTERISTICS ( $T_j=25^\circ\text{C}$ , unless otherwise stated)

PARAMETER	SYMBOL	CONDITIONS	MIN		TYP	MAX	UNIT
			UT134F	UT134G			
Critical rate of rise of Off-state voltage	$dV_D / dt$	$V_{DM} = 67\% V_{DRM(\text{max})}; T_j = 125^\circ\text{C};$ exponential waveform; gate open circuit	50	200	250		V/ $\mu$ s
Critical rate of change of Commutating voltage	$dV_{com} / dt$	$V_{DM}=400\text{V}; T_j=95^\circ\text{C}; I_{T(\text{RMS})}=4\text{A};$ $dI_{com} / dt = 1.8\text{A/ms}$ ; gate open circuit		10	50		V/ $\mu$ s
Gate controlled turn-on time	$t_{gt}$	$I_{TM} = 6 \text{ A}; V_D = V_{DRM(\text{max})};$ $I_G=0.1\text{A}; dI_G/dt=5\text{A}/\mu\text{s}$			2		$\mu$ s

## TYPICAL CHARACTERISTICS

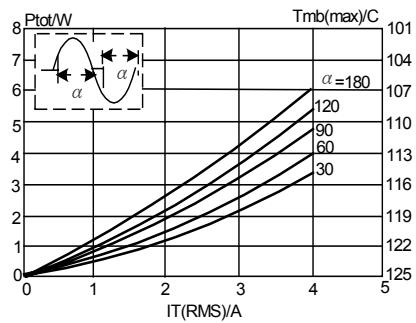


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $IT(RMS)$ , where  $\alpha$  = conduction angle.

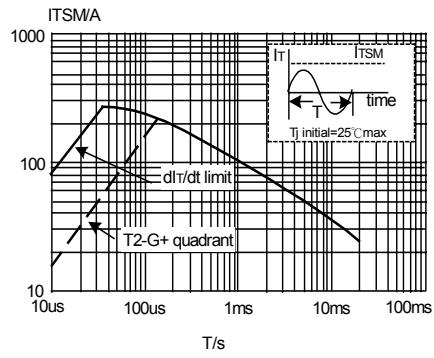


Fig.2. Maximum Permissible non-repetitive peak on-state Current  $ITSM$ , versus pulse width  $t_p$  for sinusoidal currents,  $t_p \leq 20\text{ms}$

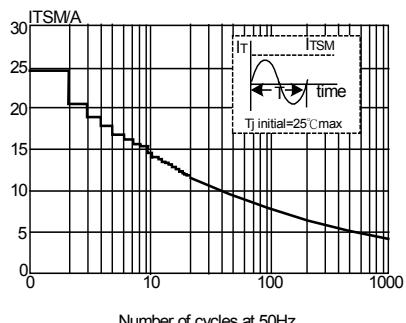


Fig.3. Maximum Permissible non-repetitive peak on-state current  $ITSM$ , versus number of cycles, for sinusoidal currents,  $f=50\text{Hz}$ .

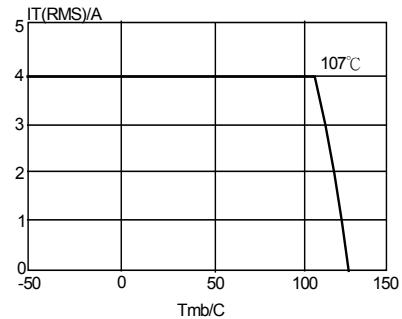


Fig.4. Maximum permissible rms current  $IT(RMS)$ , versus mounting base temperature  $T_{mb}$ .

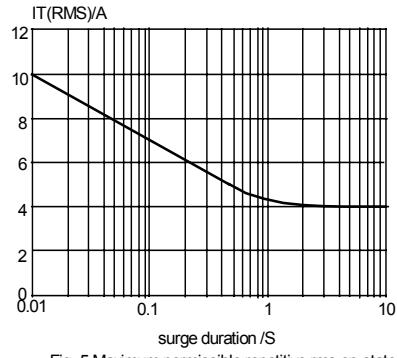


Fig. 5. Maximum permissible repetitive rms on-state current  $IT(RMS)$ , versus surge duration, for sinusoidal currents,  $f=50\text{Hz}; T_{mb} \leq 107^\circ\text{C}$

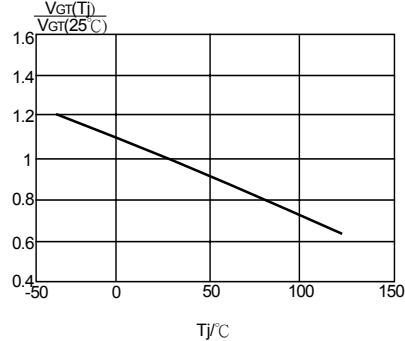


Fig.6. Normalised gate trigger voltage  $V_{GTR}(T_j)/V_{GTR}(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

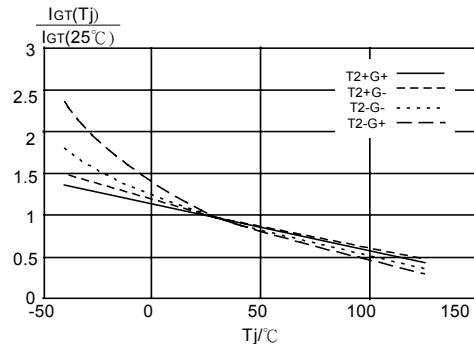


Fig. 7. Normalised gate trigger Current  
 $I_{GT}(T_j)/I_{GT}(25^\circ C)$ ,versus junction temperature  $T_j$

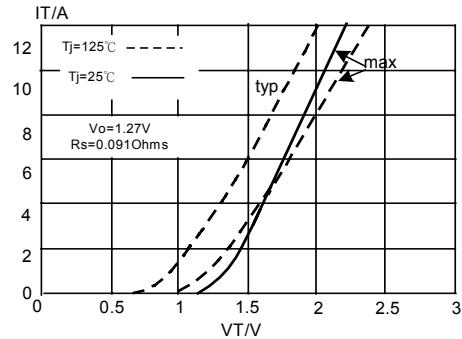


Fig.10.Typical and maximum on-state characteristic.

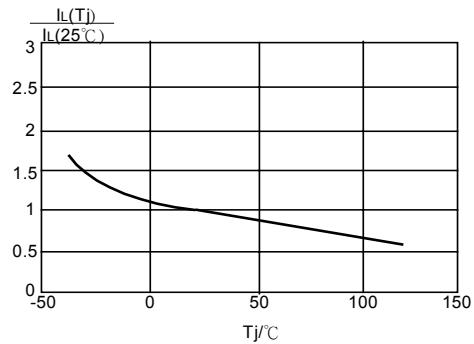


Fig.8.Normalised latching Current  $I_L(T_j)/I_L(25^\circ C)$ ,  
versus junction temperature  $T_j$

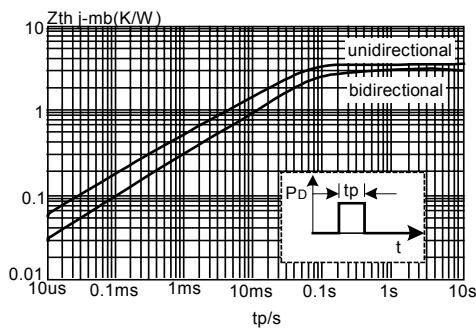


Fig.11.Transient thermal impedance  $Z_{th,i-mb}$ ,versus  
pulse width  $t_p$ .

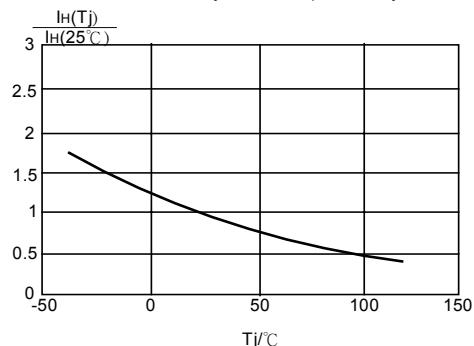


Fig. 9. Normalised holding current  $I_H(T_j)/I_H(25^\circ C)$ ,  
versus junction temperature  $T_j$

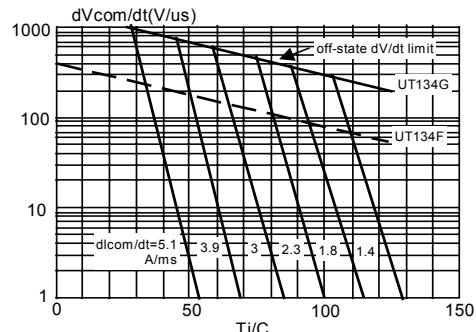


Fig.12.Typical commutation  $dV/dt$  versus junction  
temperature,parameter commutation  $dI/dt$ .The triac  
should commutate when the  $dV/dt$  is below the value  
on the appropriate curve for pre-commutation  $dI/dt$

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